

Amendments to the Specification:

Page 7, amend the paragraph beginning on line 10, to read as follows:

Now, the first embodiment of the present invention will be explained with reference to FIGS. 1 through 8. FIG. 1 is a vertical cross-sectional view of an etching apparatus according to one embodiment of a plasma processing apparatus to which the present invention is applied. On the upper area of a vacuum vessel 101 having an opened top portion are disposed a shower ~~wafer-plate~~ 102 (made for example of quartz) for introducing etching gas into the vacuum vessel 101 and a dielectric window 103 (made for example of quartz), and the area is sealed to create a processing chamber 104. The shower plate 102 has a porous structure so as to allow etching gas to flow through, and is connected to a gas feeder 105. Further, an evacuator (not shown) is connected via an evacuation opening 106 to the vacuum vessel 101. Above the dielectric window 103 is disposed a cylindrical wall 107 having a diameter substantially equal to the processing chamber 104 and in electrical contact with the processing chamber 104. At the upper opening of the cylindrical wall 107 is disposed a top plate 108 electrically connected with the wall 107 and having a round opening at the center thereof. The dielectric window 103, the cylindrical wall 107 and the top plate 108 surround and define a cylindrical space 109.